

### Abstract of the Disclosure

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10 A semiconductor device having bonding pad electrode or  
electrodes of a multi-layer structure. The bonding pad  
electrode comprises a lower electrode layer formed on a  
semiconductor substrate, and a cover insulating film formed on  
the lower electrode layer. The cover insulating film has an  
opening for exposing at least a portion of the lower electrode  
layer. A step portion is provided at a side wall of the opening of  
the cover insulating film. The size of the opening at the upside  
portion of a step surface of the step portion is larger than the  
15 size of the opening at the downside portion of the step surface.  
The bonding pad electrode further comprises an upper electrode  
layer formed on the portion of the lower electrode layer exposed  
via the opening. The upper electrode layer is made of material  
having corrosion resistance against the substance which is  
20 corrosive to the lower electrode layer, and the upper electrode  
layer overlaps the step surface of the step portion.